UNIVERSITY OF THE PUNJAB

B.S. 4 Years Program / Fourth Semester - 2019

Roli No. in Words.

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Paper: Basic Electronics
Course Code: PHY-203 / PHY-22331 Part – I (Compulsory) Time: 15 Min. Marks: 10

`\Signature of Supdt.:

ATTEMPT THIS PAPER ON THIS QUESTION SHEET ONLY.

Division of marks is given in front of each question.

This Paper will be collected back after expiry of time limit mentioned above.

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Q.1. I	Encircle the right answer cutting and o	ver	writing is	not a	llow	ed. (10x1=10)			
(i) (a)	At room temperature, the current in an intrinsic sholes (b) electrons		conductor is	due to	(d)	holes and electrons			
/!!\	With and a DC course a clienter simulate recombles	•••							
(ii) (a)	Without a DC source, a clipper circuit resembles clamper (b) rectifier		voltage do	ubler	(d)	none as above			
(iii)	If both the emitter-base and the collector-base j the transistor is in the	unct	ions of a bi	ipolar tr	ansis	tor are forward biased,			
(a)	active region (b) saturated region	(c)	cut-off reg	ion	(d)	inverse mode			
(iv)	The biasing technique that produces the most un	stab	le O-point is	s					
	collector bias (b) emitter bias		base bias		(d)	voltage-divider bias			
(v)	In a certain voltage-divider biased npn transapproximately	sisto	r, V _B is 2.	.95 V.	The	dc emitter voltage is			
(a)	2.25 V (b) 2.95 V	(c)	3.65 V		(d)	0.7 V			
(vi)	The disadvantage of base bias is that								
(a)			(b)	it prod	uces	low gain			
(c)	•		(d)			high leakage current			
(vii)	In a voltage-divider biased <i>npn</i> transistor, if the upper voltage-divider resistor (the one connected to V_{CC}) opens,								
(a)			(b)	the tra	nsisto	or goes into saturation			
(c)			(d)	the sup	oply v	oltage is too high			
(viii)	The input resistance of a common-base (CB) am	plifi	ier is						
(a)		•	(b)	very lo	w				
(c)	the same as a CE		(d)	the sar	ne as	a CC			
(ix)	A small-signal amplifier								
(a)		:	(b)	always	s has	Vout in the mV range			
(c)						CE amplifier			
(x)	The channel of a JFET is between the								
(a)			(b)	drain a	and so	ource			
(c)	gote and cource		ίď	input s	and o	utout			



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B.S. 4 Years Program / Fourth Semester – 2019

Paper: Basic Electronics Course Code: PHY-203 / PHY-22331 Part - II

Time: 2 Hrs. 45 Min. Marks: 50

ATTEMPT THIS (SUBJECTIVE) ON THE SEPARATE ANSWER SHEET PROVIDED

Q.2.		Write short answers of the following questions:	$(2 \times 10 = 20)$					
		i. What is peak reverse voltage (PRV)?						
		ii. Draw the circuit diagram of a voltage doubler circuit.	ge doubler circuit.					
		iii. Define the terms h_{ie} and h_{fe} .	Define the terms h_{ie} and h_{fe} . If $h_{fe} = 60$ and $I_C = 15$ mA, what is the value of I_B and I_E ?					
		iv. If $h_{fe} = 60$ and $I_C = 15$ mA, what is the value of I_B and I_E ?						
		v. What do you mean by the term transconductance?	What do you mean by the term transconductance? What is the cause of reverse saturation current?					
		vi. What is the cause of reverse saturation current?						
		vii. Why the common collector circuit called an emitter follower	lector circuit called an emitter follower?					
		viii. What bias conditions must exist for a transistor to operate a	is an amplifier?					
		ix. Write down the role of input coupling capacitor in a transis	tor amplifier?					
		x. What are two famous modes of operation for a MOSFET?						
Q.3:	(a) (b)	Explain what the barrier potential is and how it is created in a pn ju Discuss the circuit operation of a positive biased diode clipper and						
		voltage waveform.	(6, 4)					
Q.4:	(a)	Draw the circuit for the common-emitter (CE) transistor amplifier, and derive expressions for its Current Gain, and the Voltage Gain.						
	(b)	Trace the circuit diagram of a common-emitter (CE) self biased circuit and discuss						
		its circuit operation.	(6, 4)					
Q.5:	(a)	Explain the construction, symbol, working and characteristics of p -	-channel JFET.					
	(b)	What is the construction difference between a JFET and MOSFET.	? (7,3)					